

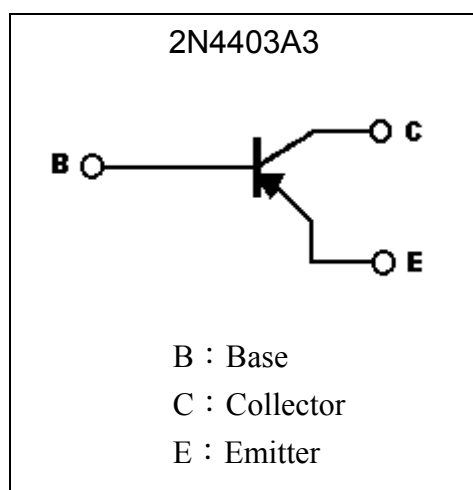
General Purpose PNP Epitaxial Planar Transistor

2N4403A3

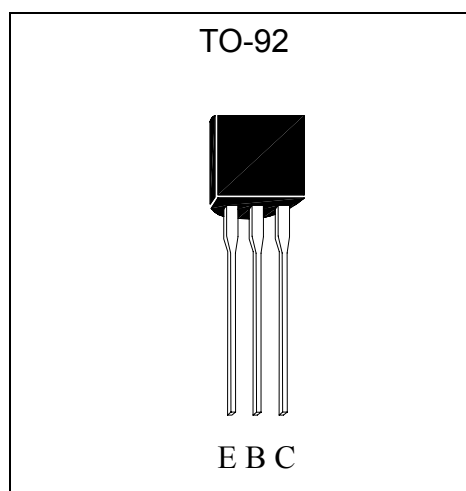
Description

- The 2N4403A3 is designed for using in driver stage of AF amplifier and general purpose amplification.
- Large I_C , $I_{C\text{ Max.}} = -0.6\text{A}$
- Low $V_{CE(\text{sat})}$, typically -0.2V at $I_C/I_B = -300\text{mA} / -30\text{mA}$. Ideal for low-Voltage operation
- Complementary to 2N4401A3.

Symbol



Outline



Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-0.6	A
Power Dissipation	P_d	625	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$

**Characteristics** (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	-40	-	-	V	I _C =-100μA
BV _{CEO}	-40	-	-	V	I _C =-1mA
BV _{EB0}	-5	-	-	V	I _E =-100μA
ICEX	-	-	-0.1	μA	V _{CE} =-35V, V _{EB} =-0.4V
*V _{CE(sat)} 1	-	-	-0.4	V	I _C =-150mA, I _B =-15mA
*V _{CE(sat)} 2	-	-	-0.75	V	I _C =-500mA, I _B =-50mA
*V _{BE(sat)} 1	-0.75	-	-0.95	V	I _C =-150mA, I _B =-15mA
*V _{BE(sat)} 2	-	-	-1.3	V	I _C =-500mA, I _B =-50mA
h _{FE} 1	30	-	-	-	V _{CE} =-1V, I _C =-0.1mA
h _{FE} 2	60	-	-	-	V _{CE} =-1V, I _C =-1mA
h _{FE} 3	100	-	-	-	V _{CE} =-1V, I _C =-10mA
*h _{FE} 4	82	-	390	-	V _{CE} =-2V, I _C =-150mA
*h _{FE} 5	20	-	-	-	V _{CE} =-2V, I _C =-500mA
f _T	200	-	-	MHz	V _{CE} =-10V, I _C =-20mA, f=100MHz
Cob	-	-	8.5	pF	V _{CB} =-10V, f=1MHz

*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

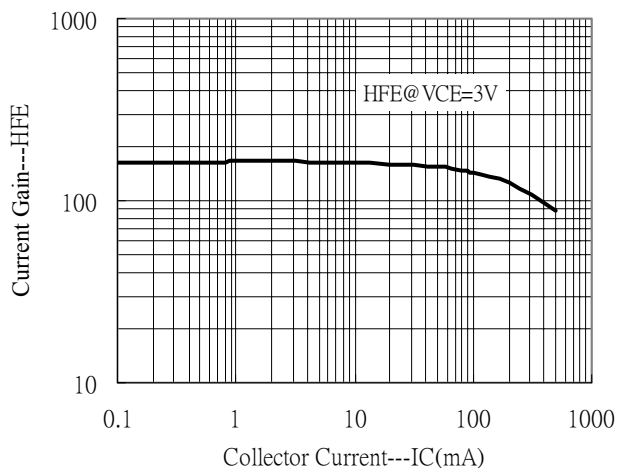
Classification Of h_{FE} 4

Rank	P	Q	R
Range	82~180	120~270	180~390

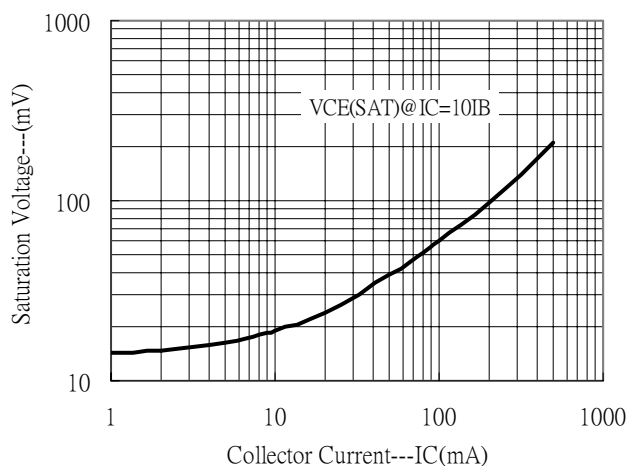


Characteristic Curves

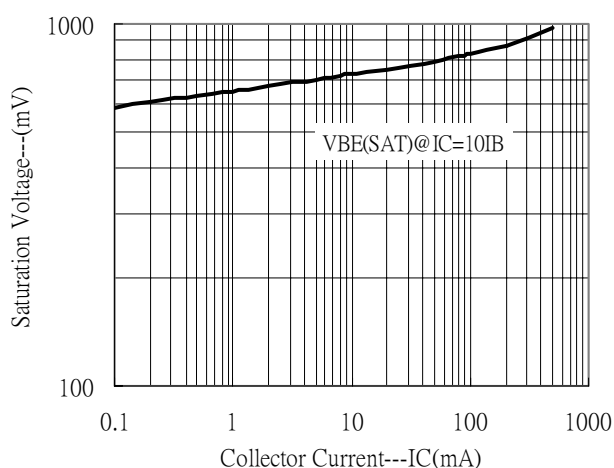
Current Gain vs Collector Current



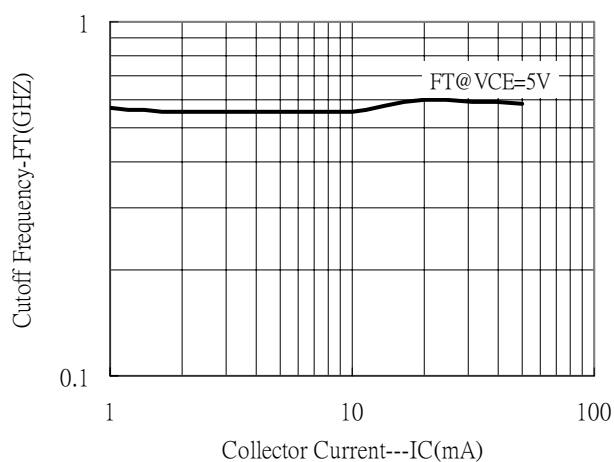
Saturation Voltage vs Collector Current



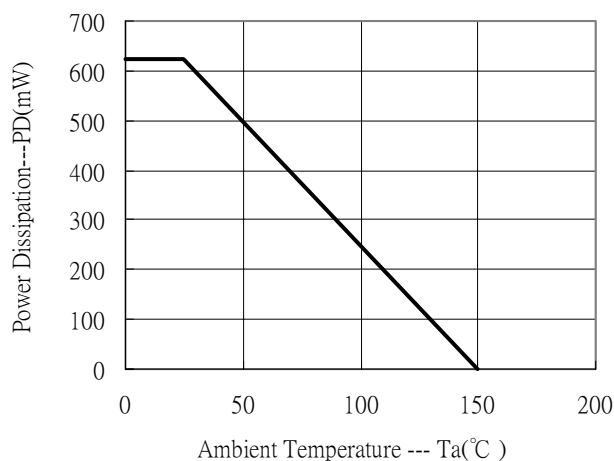
Saturation Voltage vs Collector Current



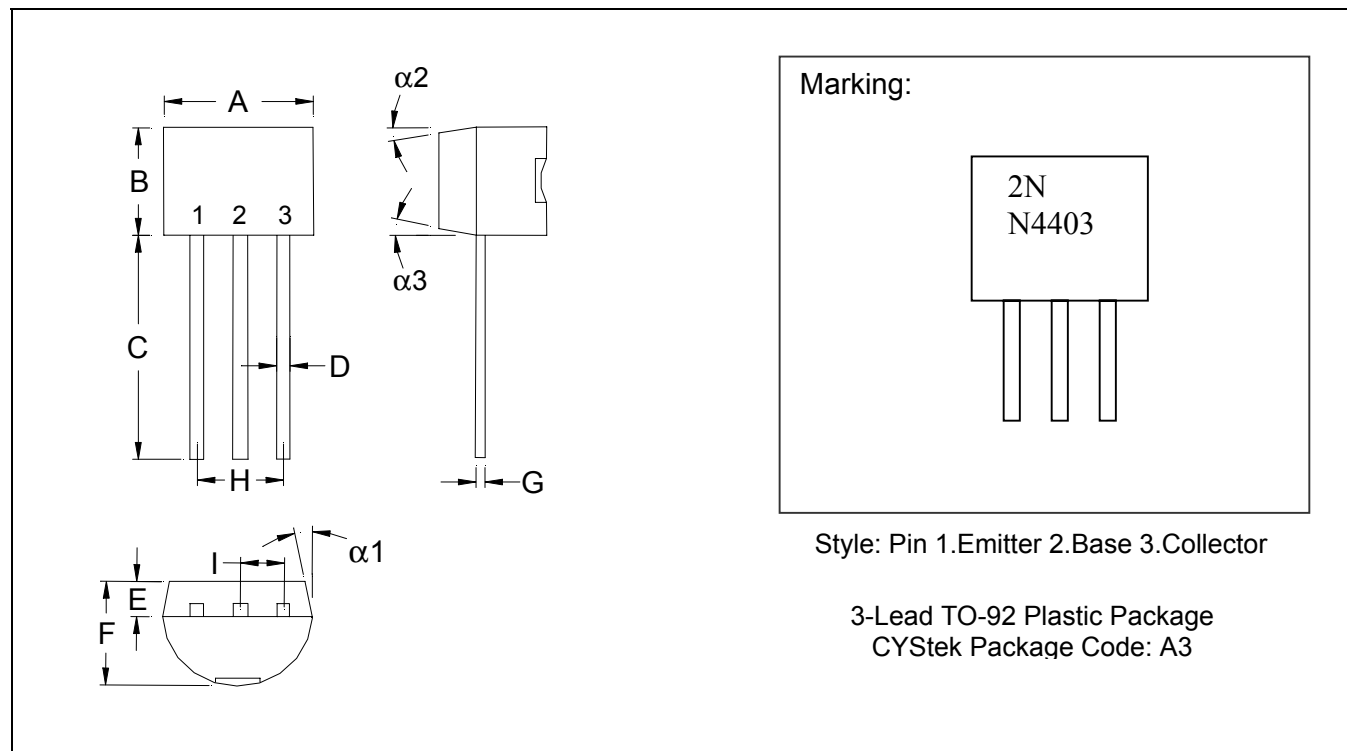
Cutoff Frequency vs Collector Current



Power Derating Curve



TO-92 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1704	0.1902	4.33	4.83	G	0.0142	0.0220	0.36	0.56
B	0.1704	0.1902	4.33	4.83	H	-	*0.1000	-	*2.54
C	0.5000	-	12.70	-	I	-	*0.0500	-	*1.27
D	0.0142	0.0220	0.36	0.56	$\alpha 1$	-	*5°	-	*5°
E	-	*0.0500	-	*1.27	$\alpha 2$	-	*2°	-	*2°
F	0.1323	0.1480	3.36	3.76	$\alpha 3$	-	*2°	-	*2°

Notes: 1. Controlling dimension: millimeters.

2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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